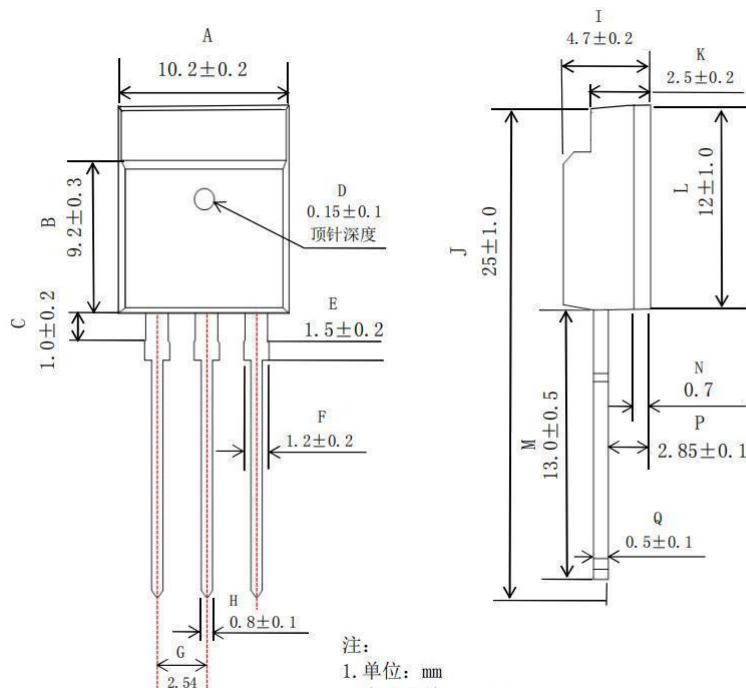


### ◆ Features:

- ✧ Fast switching speed  
开关速度快
- ✧ High input impedance and low level drive  
高输入阻抗和低电平驱动
- ✧ Avalanche energy tested  
雪崩能量测试
- ✧ Improved dv/dt capability, high ruggedness  
提高 dv/dt 能力, 高耐用性

### ◆ Applications

- ✧ High efficiency switch mode power supplies  
高效率开关电源
- ✧ Power factor correction  
功率因数校正
- ✧ Electronic lamp ballast  
电子整流器


**TO-262F**


注:  
1. 单位: mm  
2. 未注公差:  $\pm 0.2\text{mm}$   
(除非另有说明)

**◆ Absolute Maximum Ratings (Tc=25°C)**

| Symbol           | Parameters                                       | Ratings    | Unit |
|------------------|--------------------------------------------------|------------|------|
| V <sub>DSS</sub> | Drain-Source Voltage<br>漏源电压                     | <b>650</b> | V    |
| V <sub>GS</sub>  | Gate-Source Voltage-Continuous<br>栅源电压           | <b>±30</b> | V    |
| I <sub>D</sub>   | Drain Current-Continuous (Note 2)<br>漏极持续电流      | <b>16</b>  | A    |
| I <sub>DM</sub>  | Drain Current-Single Plused (Note 1)<br>漏极单次脉冲电流 | <b>64</b>  | A    |
| P <sub>D</sub>   | Power Dissipation (Note 2)<br>功率损耗               | <b>62</b>  | W    |
| T <sub>j</sub>   | Max.Operating junction temperature<br>最大结温       | <b>150</b> | °C   |

**◆ Electrical characteristics (Tc=25°C unless otherwise noted)**

| Symbo<br>l                    | Parameters                                                  | Min        | Typ         | Max        | Units | Conditions                                                          |
|-------------------------------|-------------------------------------------------------------|------------|-------------|------------|-------|---------------------------------------------------------------------|
| <b>Static Characteristics</b> |                                                             |            |             |            |       |                                                                     |
| B <sub>VDSS</sub>             | Drain-Source Breakdown<br>VoltageCurrent (Note 1)<br>漏极击穿电压 | <b>650</b> | --          | --         | V     | I <sub>D</sub> =250μA,<br>V <sub>GS</sub> =0V, T <sub>J</sub> =25°C |
| V <sub>GS(th)</sub>           | Gate Threshold Voltage<br>栅极开启电压                            | <b>2.0</b> | --          | <b>4.0</b> | V     | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA            |
| R <sub>DS(on)</sub>           | Drain-Source On-Resistance<br>漏源导通电阻                        | --         | <b>0.52</b> | --         | Ω     | V <sub>GS</sub> =10V, I <sub>D</sub> =8A                            |
| I <sub>GSS</sub>              | Gate-Body Leakage Current<br>栅极漏电流                          | --         | --          | <b>±90</b> | nA    | V <sub>GS</sub> =±30V, V <sub>DS</sub> =0                           |
| I <sub>DSS</sub>              | Zero Gate Voltage Drain Current<br>零栅极电压漏极电流                | --         | --          | <b>200</b> | nA    | V <sub>DS</sub> =650V, V <sub>GS</sub> =0                           |
| g <sub>fs</sub>               | Forward Transconductance<br>正向跨导                            | --         | <b>6.0</b>  | --         | S     | V <sub>DS</sub> =30V, I <sub>D</sub> =8A                            |

**OSPH16N65****650V N-CHANNEL MOSFET**

| Switching Characteristics |                                                                         |    |      |      |      |                                                                                      |
|---------------------------|-------------------------------------------------------------------------|----|------|------|------|--------------------------------------------------------------------------------------|
| T <sub>d (on)</sub>       | Turn-On Delay Time<br>开启延迟时间                                            | -- | 16   | --   | ns   | V <sub>DS</sub> =325V, I <sub>D</sub> =16A,<br>R <sub>G</sub> =25Ω（Note 2）           |
| T <sub>r</sub>            | Rise Time<br>上升时间                                                       | -- | 45   | --   | ns   |                                                                                      |
| T <sub>d (off)</sub>      | Turn-Off Delay Time<br>关闭延迟时间                                           | -- | 85   | --   | ns   |                                                                                      |
| T <sub>f</sub>            | Fall Time<br>下降时间                                                       | -- | 18   | --   | ns   |                                                                                      |
| Q <sub>g</sub>            | Total Gate Charge<br>栅极总电荷                                              | -- | 55   | --   | nC   | V <sub>DS</sub> =520V<br>，<br>V <sub>GS</sub> =0-10V，<br>I <sub>D</sub> =16A（Note 2） |
| Q <sub>gs</sub>           | Gate-Source Charge<br>栅源极电荷                                             | -- | 15   | --   | nC   |                                                                                      |
| Q <sub>gd</sub>           | Gate-Drain Charge<br>栅漏极电荷                                              | -- | 21   | --   | nC   |                                                                                      |
| Dynamic Characteristics   |                                                                         |    |      |      |      |                                                                                      |
| C <sub>iss</sub>          | Input Capacitance<br>输入电容                                               | -- | 2800 | --   | pF   | V <sub>DS</sub> =25V， V <sub>GS</sub> =0，<br>f=1MHz                                  |
| C <sub>oss</sub>          | Output Capacitance<br>输出电容                                              | -- | 380  | --   | pF   |                                                                                      |
| C <sub>rss</sub>          | Reverse Transfer Capacitance<br>反向传输电容                                  | -- | 20   | --   | pF   |                                                                                      |
| I <sub>S</sub>            | Continuous Drain-Source Diode<br>Forward Current（Note 2）<br>二极管导通正向持续电流 | -- | --   | 16   | A    |                                                                                      |
| V <sub>SD</sub>           | Diode Forward On-Voltage<br>二极管正向导通电压                                   | -- | --   | 0.9  | V    | I <sub>S</sub> =1A， V <sub>GS</sub> =0                                               |
| R <sub>th(j-c)</sub>      | Thermal Resistance, Junction to Case<br>结到外壳的热阻                         | -- | --   | 2.02 | °C/W |                                                                                      |

Note 1: Repetitive Rating : Pulse width limited by maximum junction temperature

Note 2: Pulse test: PW ≤ 300us , duty cycle ≤ 2%.